Abstracts

A Nonlinear GaAs FET Model for Use in the Design of Output Circuits for Power Amplifiers (1985 [MWSYM])

W.R. Curtice and M. Ettenberg. "A Nonlinear GaAs FET Model for Use in the Design of Output Circuits for Power Amplifiers (1985 [MWSYM])." 1985 MTT-S International Microwave Symposium Digest 85.1 (1985 [MWSYM]): 405-408.

A nonlinear equivalent circuit model for the GaAs FET has been developed based upon the small-signal device model and separate current measurements, including drain-gate avalanche current data. The harmonic balance technique is used to develop the FET rf load-pull characteristics in an amplifier configuration under large signal operation. Computed and experimental load-pull results show good agreement.

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